

**N-Ch MOSFET** 

ID

60A

# **General Description**

The WSR60N06 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

# Application

**BVDSS** 

60V

- Power switching application
- LED backlighting

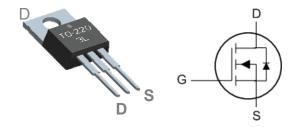
**Product Summery** 

Uninterruptible power supply

#### **Features**

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **TO-220AB Pin Configuration**



**RDSON** 

 $12m\Omega$ 

# **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units	
$V_{DS}$	Drain-Source Voltage	60	V	
$V_{GS}$	Gate-Source Voltage	±20	V	
I <sub>D</sub> @T <sub>C</sub> =25℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	60	Α	
I <sub>D</sub> @T <sub>C</sub> =100℃	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	41	Α	
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	120	Α	
EAS	Single Pulse Avalanche Energy <sup>3</sup>	290	mJ	
P <sub>D</sub> @T <sub>C</sub> =25℃	T <sub>C</sub> =25 °C Total Power Dissipation <sup>4</sup> 85		W	
T <sub>J</sub> T <sub>STG</sub>	Operating Junction Temperature Range	-55 to 150	$^{\circ}$	

#### **Thermal Data**

Symbol	Parameter	Тур.	Max.	Unit	
$R_{ heta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>		62	°C/W	
$R_{ heta JC}$	Thermal Resistance Junction-Case <sup>1</sup>		0.57	°C/W	



# Electrical Characteristics (T<sub>J</sub>=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =250uA	60			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA		0.057		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =30A		12	14	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =20A		15	20	
$V_{GS(th)}$	Gate Threshold Voltage	-V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	2.0	3.0	4.0	V
$\triangle V_{GS(th)}$	V <sub>GS(th)</sub> Temperature Coefficient			-5.68		mV/℃
I <sub>DSS</sub>	Drain Source Lookage Current	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25℃			1	uA
	Drain-Source Leakage Current	$V_{DS}$ =48V , $V_{GS}$ =0V , $T_J$ =55 $^{\circ}$ C			5	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm 20 V$ , $V_{DS}$ = $0 V$			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =15A		30		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		1.7	3.4	Ω
$Q_{g}$	Total Gate Charge (4.5V)	V <sub>DS</sub> =30V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =30A		36	45	nC
$Q_gs$	Gate-Source Charge			9.9	18	
Q <sub>gd</sub>	Gate-Drain Charge			6.6	15	
T <sub>d(on)</sub>	Turn-On Delay Time	$V_{DS}$ =30V , $V_{GS}$ =10V , $I_{D}$ =2A , R=1 $\Omega$ .		12	14.4	
Tr	Rise Time			5.2	10	
T <sub>d(off)</sub>	Turn-Off Delay Time			38	55	ns
T <sub>f</sub>	Fall Time			27	32	
Ciss	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , f=1MHz		2498		
C <sub>oss</sub>	Output Capacitance			185		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			80		

#### **Diode Characteristics**

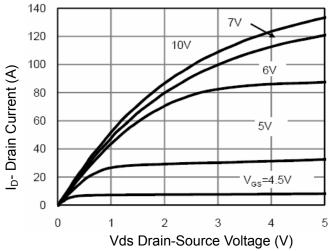
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,6</sup>	$V_G$ = $V_D$ = $0V$ , Force Current			38	Α
I <sub>SM</sub>	Pulsed Source Current <sup>2,6</sup>				90	Α
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25℃			1.2	V
t <sub>rr</sub>	Reverse Recovery Time	- IF=1A ,dl/dt=100A/μs,TJ=25℃		35		nS
Q <sub>rr</sub>	Reverse Recovery Charge			47		nC

#### Notes:

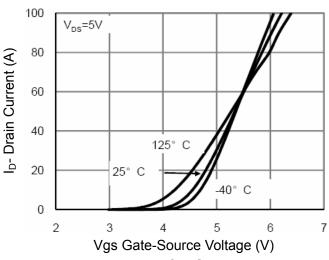
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E<sub>AS</sub> condition: Tj=25  $^{\circ}$ C,V<sub>DD</sub>=30V,V<sub>G</sub>=10V,L=0.5mH,Rg=25

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# **Typical Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

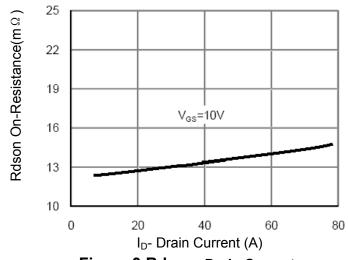


Figure 3 Rdson- Drain Current

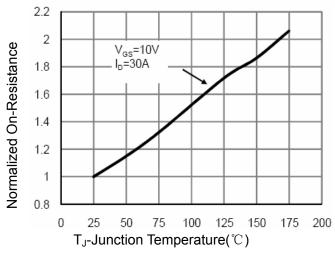


Figure 4 Rdson-JunctionTemperature

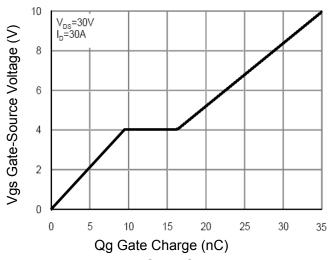


Figure 5 Gate Charge

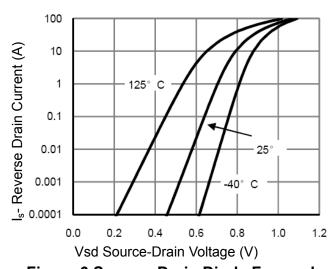


Figure 6 Source- Drain Diode Forward



**N-Ch MOSFET** 

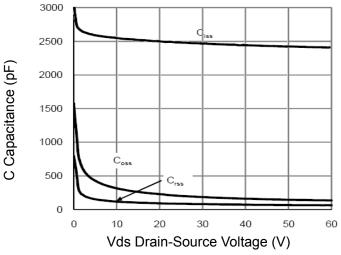


Figure 7 Capacitance vs Vds

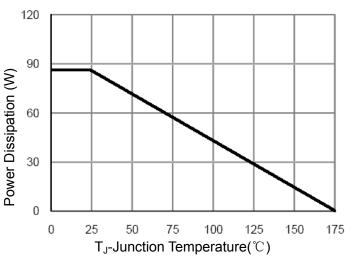


Figure 9 Power De-rating

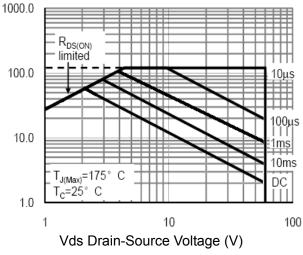


Figure 8 Safe Operation Area

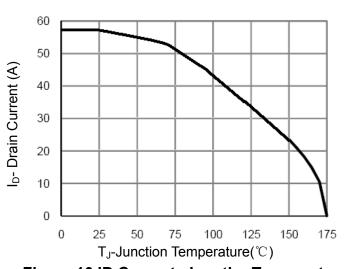
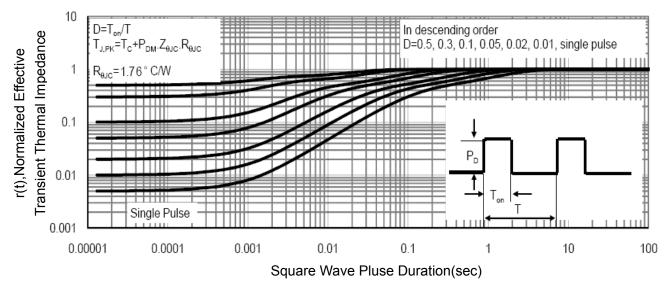


Figure 10 ID Current- JunctionTemperature



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



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